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## Electrical characterization of ruthenium and Iridium Schottky contacts on n-Ge (100)

Ruthenium (Ru) and Iridium (Ir) Schottky barrier diodes were electron beam deposited on (100) n-type germanium. Electrical characterization of these contacts using current-voltage and capacitance-voltage measurements was performed under various annealing conditions. The variation of the electrical properties of these Schottky contacts can be attributed to the combined effects of interfacial reactions and phase transition during the annealing process.

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